AMENDMENTS TO THE CLAIMS

- 1. (Currently amended) A device comprising:
 - an emitter electrode;
 - a resistor layer;
 - an electrically conductive seed layer overlying part of the resistor layer, the seed layer including a plurality of laterally separated sections;
 - a dielectric layer overlying the resistive layer;
 - a gate electrode overlying the dielectric layer above the resistive layer and having lateral edges in approximate vertical alignment with lateral edges of the dielectric layer; and
 - a <u>plurality of carbon based electron-emissive elements</u> <u>element</u> (a) positioned over the sections of the seed layer above the emitter electrode and (b) situated in a composite opening extending through the gate electrode and the dielectric layer.
- 2. (Currently amended) A device comprising:
 - an emitter electrode;
 - an electrically resistive layer overlying at least a portion of the emitter electrode;
 - a dielectric layer overlying the resistive layer;
 - a plurality of laterally separated gate electrodes overlying the dielectric layer above the resistive layer; and
 - for each gate electrode, a multiplicity of electron-emissive elements (a) grown from a seed layer that includes a plurality of unconnected sections above the emitter electrode and (b) situated in composite openings extending through the gate electrode electrodes and the dielectric layer.

- 3. (Original) A device as in Claim 2 wherein the dielectric layer comprises a dual layer of silicon nitride and silicon dioxide.
- 4. (Previously presented) A device as in Claim 2, wherein the dielectric layer comprises a single layer of silicon nitride.
- 5. (Previously presented) A device as in Claim 2, wherein the dielectric layer comprises a single layer of silicon dioxide.
- 6. (Original) A device as in Claim 2 wherein the multiplicity of electron-emissiveelements comprise carbon.
- 7. (Original) A device as in Claim 6 wherein the multiplicity of electron-emissiveelements are filaments.

8-9. (Canceled)

- 10. (Previously presented) A device as in Claim 2, wherein the electron-emissive elements positioned over at least two sections of the seed layer defines a single pixel of a display system.
- 11. (Previously presented) A device as in Claim 10, wherein the electron-emissive elements are allocated into a number of laterally separated sets, each set comprising multiple electron-emissive elements overlying at least one of the sections of the seed layer.

12. (Canceled)

13. (Previously presented) An electron-emitting device, comprising: an emitter electrode;

- a gate electrode;
- a plurality of groups of electron-emissive elements situated in one or more openings in the gate electrode; and
- a seed layer including at least two laterally separated sections, each section of the seed layer electrically coupled between one or more groups of electron-emissive elements and the emitter electrode.
- 14. (Previously presented) The device of claim 13, further comprising:

 an electrically resistive layer overlying at least a portion of the emitter electrode, the

 electrically resistive layer electrically coupled in series between the emitter

 electrode and the seed layer.
- 15. (Previously presented) The device of claim 14, further comprising: a dielectric layer disposed between the electrically resistive layer and the gate electrode.
- 16. (Previously presented) The device of claim 15, wherein the dielectric layer comprises silicon nitride.
- 17. (Previously presented) The device of claim 15, wherein the dielectric layer comprises silicon dioxide.
- 18. (Previously presented) The device of claim 15, wherein the dielectric layer comprises a layer of silicon nitride and a layer of silicon dioxide.
- 19. (Previously presented) The device of claim 13, wherein the electron-emissive elements comprise carbon.

- 20. (Previously presented) The device of claim 13, wherein the electron-emissive elements comprise a number of carbon filaments.
- 21. (Previously presented) The device of claim 13, wherein the sections of the seed layer symmetrically over-align with the openings of the gate electrode.
- 22. (Previously presented) The device of claim 13, wherein multiple sections of the seed layer correspond to a single pixel of a display system.
- 23. (Previously presented) The device of claim 13, wherein multiple sections of the seed layer correspond to a single color for a pixel of a display system.